

General Description

The 05N03A uses advanced trench technology and design to provide excellent RDS(ON). This device is ideal for PWM, load switching and general purpose applications.

Features

- Low On-Resistance
- High Reliability Capability with Passivation
- 100% avalanche tested
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current	64	A
I_{DM}	Pulsed Drain Current	240	A
EAS	Single Pulse Avalanche Energy	220	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation	75	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	50	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	3.4	$^\circ C/W$

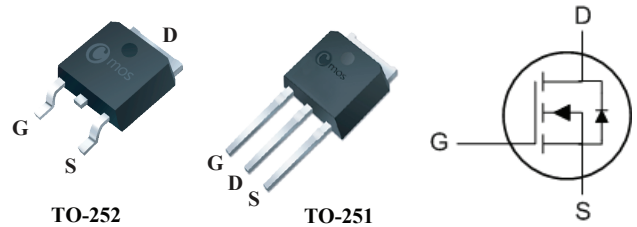
Product Summary

BVDSS	RDSON	ID
30V	4.5m Ω	80A

Applications

- DC-DC Converters
- Power switching application

TO-252/251 Pin Configuration



Type	Package	Marking
CMD05N03A	TO-252	CMD05N03A
CMU05N03A	TO-251	CMU05N03A

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=28A$	---	---	4.5	m Ω
		$V_{GS}=4.5V, I_D=20A$	---	---	6.8	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=15A$	---	33	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.1	---	Ω
Q_g	Total Gate Charge	$V_{DS}=15V, V_{GS}=4.5V, I_D=30A$	---	15	---	nC
Q_{gs}	Gate-Source Charge		---	7	---	
Q_{gd}	Gate-Drain Charge		---	3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=15V, V_{GS}=4.5V$ $R_G=3\Omega, I_{DS}=15A$	---	15	---	ns
T_r	Rise Time		---	21	---	
$T_{d(off)}$	Turn-Off Delay Time		---	22	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	2400	---	pF
C_{oss}	Output Capacitance		---	765	---	
C_{rss}	Reverse Transfer Capacitance		---	30	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	80	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=20A, T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

This product has been designed and qualified for the consumer market.
Cmos assumes no liability for customers' product design or applications.
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